

SANYO	No.1583B	LB1494
		Monolithic Digital IC Level Meter for FLT Display

Use

- . DC level meters such as signal meters

Features and Functions

- . Wide supply voltage range (4.0 to 16V)
- . FLT direct drive capability
- . On-chip pull-down resistors (Pull-down current can be varied by external resistor Rpd.)
- . On-chip voltage reference
- . Especially suited for DC signal meter use because of on-chip comparators with hysteresis

Absolute Maximum Ratings at Ta=25°C

Maximum Supply Voltage	V _{CCmax}	GND=0V	18	unit	V
Maximum Supply Voltage	V _{EE}	V _{EE} ≤ GND	V _{CC} -35		V
Output Supply Voltage	V _{OUT}		V _{EE} to V _{CC}		V
Input Supply Voltage	V _{IN}		GND to V _{CC}		V
Output Current	I _{OUT}		10		mA
Pull-down Current	I _{pd}		1.0		mA
Allowable Power Dissipation	P _{dmax}		960		mW
Operating Temperature	Topg		-25 to +60		°C
Storage Temperature	Tstg		-55 to +125		°C

Allowable Operating Condition at Ta=25°C

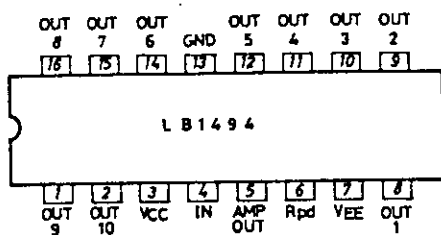
Supply Voltage	V _{CC}	GND=0V	4.0 to 16	unit	V
	V _{EE}	V _{EE} ≤ GND	V _{CC} -5 to V _{CC} -35		V

Electrical Characteristics at Ta=25°C, V_{CC}=6.0V, GND=0V, V_{EE}=-24V, Rpd=91kohms

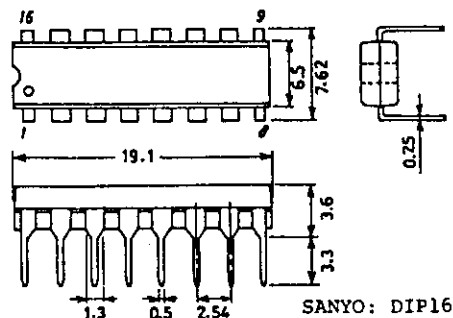
Current Dissipation	I _{CC}	V _{IN} =0V	min	typ	max	unit
Sensitivity	V _{IN}	V _{CS} -ON level	560	610	660	mV

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Pin Assignment



Package Dimensions 3064 (unit: mm)



Specifications and information herein are subject to change without notice.

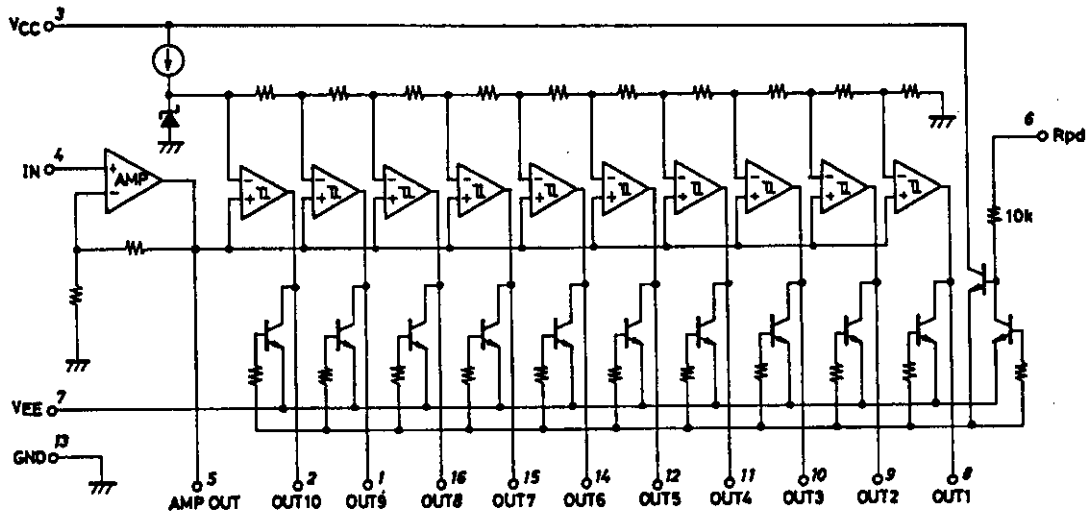
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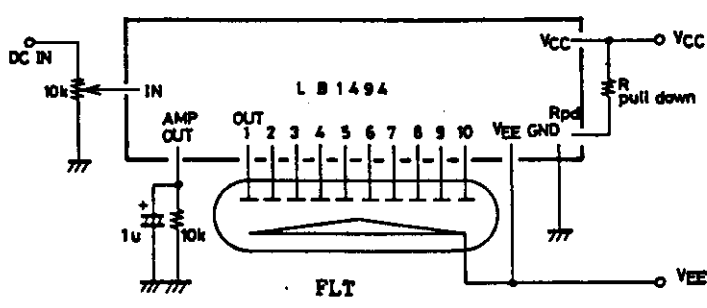
			min	typ	max	unit
Comparator Level 1*	V _{C1}		0.17	0.2V _{C5}	0.23	mV
Comparator Level 2	V _{C2}		0.35	0.4V _{C5}	0.45	mV
Comparator Level 3	V _{C3}		0.52	0.6V _{C5}	0.68	mV
Comparator Level 4	V _{C4}		0.70	0.8V _{C5}	0.90	mV
Comparator Level 5	V _{C5}	Adjust point		V _{IN}		mV
Comparator Level 6	V _{C6}		1.1	1.2V _{C5}	1.3	mV
Comparator Level 7	V _{C7}		1.3	1.4V _{C5}	1.5	mV
Comparator Level 8	V _{C8}		1.5	1.6V _{C5}	1.7	mV
Comparator Level 9	V _{C9}		1.7	1.8V _{C5}	1.9	mV
Comparator Level 10	V _{C10}		1.9	2.0V _{C5}	2.1	mV
Output Saturation Voltage	V _{O(sat)}	I _{OUT} =-10mA	V _{CC} -1.2			V
Input Bias Current	I _{INO}		-1.0			uA
Comparator Hysteresis	V _{CC(hys)}		18	26	34	mV
Pull-down Current	I _{pd}	V _{OUT} =V _{CC}		0.3		mA

*: The comparator level represents the compare point when the input is changed from low level to high level.

Equivalent Circuit

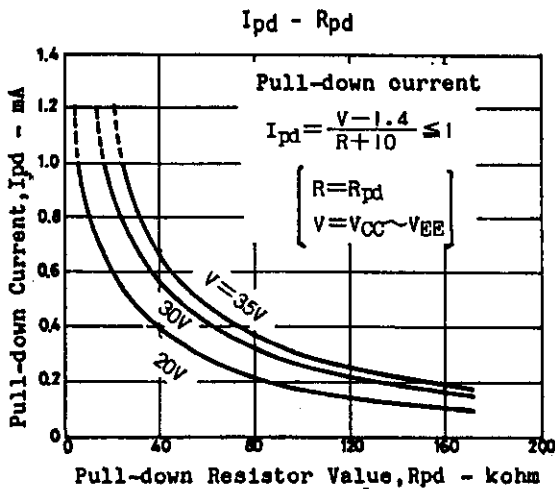


Sample Application Circuit: Signal Meter



Pin Description

Pin Name	Pin No.	Function
V _{CC}	3	Power supply pin. The voltage on all other pins must not exceed this V _{CC} value. The voltage across V _{CC} and GND is 4.0 to 16V.
I _N	4	Input pin for level displaying signal. Since this pin has a high input impedance, a pull-down resistor of several kohms must be connected across this pin and GND.
V _{EE}	7	Connected to FLT cathode. The voltage on all other pins must exceed this V _{EE} value. The voltage across V _{CC} and V _{EE} is 5.0 to 35V.
GND	13	GND for signal line. A level displaying signal is applied between GND and I _N . If 5.0V ≤ V _{CC} to V _{EE} ≤ 16V, this pin and V _{EE} can be at the same potential.
Amp OUT	5	An input signal is amplified approximately 1.7 times and is delivered at this pin. Since this output is of emitter follower type, a load resistor of 10kohms must be connected across this pin and GND. The response time can be controlled by the time constant which is provided by a capacitor of several uF to several tens of uF connected in parallel.
OUT 1 to OUT 10	1,2 8to12 14to16	Connected to FLT grid or anode. FLT is lighted in approximately 120mV-step in the order of increasing level as OUT1, OUT2, -----, OUT10.
Rpd	6	Pin used to determine pull-down current I _{pd} . Pull-down current I _{pd} is determined by a resistor connected across this pin and V _{CC} and voltage across V _{CC} and V _{EE} . Assuming the value of a resistor connected across V _{CC} and Rpd is R(kohm) and the voltage across V _{CC} and V _{EE} is V(V), I _{pd} (mA) is calculated by the following formula. $I_{pd} = (V - 1.4) / (R + 10) \leq 1$ ----- (Refer to Fig.) It should be noted, however, that the early effect of each transistor increases the actual I _{pd} several %.



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